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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	109000
Total RAM Bits	7782400
Number of I/O	170
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	325-LFBGA, FCBGA
Supplier Device Package	325-FCBGA (11x11)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf100tl-fcsg325i

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2 Overview

This datasheet describes PolarFire® FPGA device characteristics with industrial temperature range (–40 °C to 100 °C T_J) and extended commercial temperature range (0 °C to 100 °C T_J). The devices are provided with a standard speed grade (STD) and a –1 speed grade with higher performance. The FPGA core supply V_{DD} can operate at 1.0 V for lower-power or 1.05 V for higher performance. Similarly, the transceiver core supply V_{DDA} can also operate at 1.0 V or 1.05 V. Users select the core operating voltage while creating the Libero project.

The maximum overshoot duration is specified as a high-time percentage over the lifetime of the device. A DC signal is equivalent to 100% of the duty-cycle.

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for HSIO.

Table 6 • Maximum Overshoot During Transitions for HSIO

AC (V_{IN}) Overshoot Duration as % at $T_J = 100\text{ }^{\circ}\text{C}$	Condition (V)
100	1.8
100	1.85
100	1.9
100	1.95
100	2
100	2.05
100	2.1
100	2.15
100	2.2
90	2.25
30	2.3
7.5	2.35
1.9	2.4

Note: Overshoot level is for VDDI at 1.8 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for HSIO.

Table 7 • Maximum Undershoot During Transitions for HSIO

AC (V_{IN}) Undershoot Duration as % at $T_J = 100\text{ }^{\circ}\text{C}$	Condition (V)
100	-0.05
100	-0.1
100	-0.15
100	-0.2
100	-0.25
100	-0.3
100	-0.35
100	-0.4
44	-0.45
14	-0.5
4.8	-0.55
1.6	-0.6

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for GPIO.

6.2.2.1 Power-Supply Ramp Times

The following table shows the allowable power-up ramp times. Times shown correspond to the ramp of the supply from 0 V to the minimum recommended voltage as specified in the section [Recommended Operating Conditions](#) (see page 6). All supplies must rise and fall monotonically.

Table 10 • Power-Supply Ramp Times

Parameter	Symbol	Min	Max	Unit
FPGA core supply	V _{DD}	0.2	50	ms
Transceiver core supply	V _{DDA}	0.2	50	ms
Must connect to 1.8 V supply	V _{DD18}	0.2	50	ms
Must connect to 2.5 V supply	V _{DD25}	0.2	50	ms
Must connect to 2.5 V supply	V _{DDA25}	0.2	50	ms
HSIO bank I/O power supplies	V _{DDI} [0,1,6,7]	0.2	50	ms
GPIO bank I/O power supplies	V _{DDI} [2,4,5]	0.2	50	ms
Bank 3 dedicated I/O buffers (GPIO)	V _{DDI3}	0.2	50	ms
GPIO bank auxiliary power supplies	V _{DDAUX} [2,4,5]	0.2	50	ms
Transceiver reference clock supply	V _{DD_XCVR_CLK}	0.2	50	ms
Global V _{REF} for transceiver reference clocks	XCVR _{VREF}	0.2	50	ms

Note: For proper operation of programming recovery mode, if a VDD supply brownout occurs during programming, a minimum supply ramp down time for only the VDD supply is recommended to be 10 ms or longer by using a programmable regulator or on-board capacitors.

6.2.2.2 Hot Socketing

The following table lists the hot-socketing DC characteristics over recommended operating conditions.

Table 11 • Hot Socketing DC Characteristics over Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Current per transceiver Rx input pin (P or N single-ended) ^{1, 2}	XCVR _{RX_HS}			±4	mA	V _{DDA} = 0 V
Current per transceiver Tx output pin (P or N single-ended) ³	XCVR _{TX_HS}			±10	mA	V _{DDA} = 0 V
Current per transceiver reference clock input pin (P or N single-ended) ⁴	XCVR _{REF_HS}			±1	mA	V _{DD_XCVR_CLK} = 0 V
Current per GPIO pin (P or N single-ended) ⁵	I _{GPIO_HS}			±1	mA	V _{DDI_X} = 0 V
Current per HSIO pin (P or N single-ended)						Hot socketing is not supported in HSIO.

- Assumes that the device is powered-down, all supplies are grounded, AC-coupled interface, and input pin pairs are driven by a CML driver at the maximum amplitude (1 V pk–pk) that is toggling at any rate with PRBS7 data.
- Each P and N transceiver input has less than the specified maximum input current.
- Each P and N transceiver output is connected to a 40 Ω resistor (50 Ω CML termination – 20% tolerance) to the maximum allowed output voltage (V_{DDAmax} + 0.3 V = 1.4 V) through an AC-coupling capacitor with all PolarFire device supplies grounded. This shows the current for a worst-case DC coupled interface. As an AC-coupled interface, the output signal will settle at ground and no hot socket current will be seen.
- V_{DD_XCVR_CLK} is powered down and the device is driven to –0.3 V < V_{IN} < V_{DD_XCVR_CLK}.
- V_{DDI_X} is powered down and the device is driven to –0.3 V < V_{IN} < GPIO V_{DDI_{max}}.

Note: The following dedicated pins do not support hot socketing: TMS, TDI, TRSTB, DEVRST_N, and FF_EXIT_N. Weak pull-up (as specified in GPIO) is always enabled.

6.3 Input and Output

The following section describes:

- DC I/O levels
- Differential and complementary differential DC I/O levels
- HSIO and GPIO on-die termination specifications
- LVDS specifications

6.3.1 DC Input and Output Levels

The following tables list the DC I/O levels.

Table 12 • DC Input Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{IL} Min (V)	V _{IL} Max (V)	V _{IH} Min (V)	V _{IH} ¹ Max (V)
PCI	3.15	3.3	3.45	−0.3	0.3 x V _{DDI}	0.5 x V _{DDI}	3.45
LVTTL	3.15	3.3	3.45	−0.3	0.8	2	3.45
LVC MOS33	3.15	3.3	3.45	−0.3	0.8	2	3.45
LVC MOS25	2.375	2.5	2.625	−0.3	0.7	1.7	2.625
LVC MOS18	1.71	1.8	1.89	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.89
LVC MOS15	1.425	1.5	1.575	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.575
LVC MOS12	1.14	1.2	1.26	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.26
SSTL25I ²	2.375	2.5	2.625	−0.3	V _{REF} − 0.15	V _{REF} + 0.15	2.625
SSTL25II ²	2.375	2.5	2.625	−0.3	V _{REF} − 0.15	V _{REF} + 0.15	2.625
SSTL18I ²	1.71	1.8	1.89	−0.3	V _{REF} − 0.125	V _{REF} + 0.125	1.89
SSTL18II ²	1.71	1.8	1.89	−0.3	V _{REF} − 0.125	V _{REF} + 0.125	1.89
SSTL15I	1.425	1.5	1.575	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	1.575
SSTL15II	1.425	1.5	1.575	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	1.575

Table 13 • DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
PCI ¹	3.15	3.3	3.45		0.1 x V _{DDI}	0.9 x V _{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVC MOS33	3.15	3.3	3.45		0.4	V _{DDI} – 0.4			
LVC MOS25	2.375	2.5	2.625		0.4	V _{DDI} – 0.4			
LVC MOS18	1.71	1.8	1.89		0.45	V _{DDI} – 0.45			
LVC MOS15	1.425	1.5	1.575		0.25 x V _{DDI}	0.75 x V _{DDI}			
LVC MOS12	1.14	1.2	1.26		0.25 x V _{DDI}	0.75 x V _{DDI}			
SSTL25I ³	2.375	2.5	2.625		V _{TT} – 0.608	V _{TT} + 0.608		8.1	8.1
SSTL25II ³	2.375	2.5	2.625		V _{TT} – 0.810	V _{TT} + 0.810		16.2	16.2
SSTL18I ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		6.7	6.7
SSTL18II ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		13.4	13.4
SSTL15I ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL15II ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
SSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		8	8
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		16	16

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

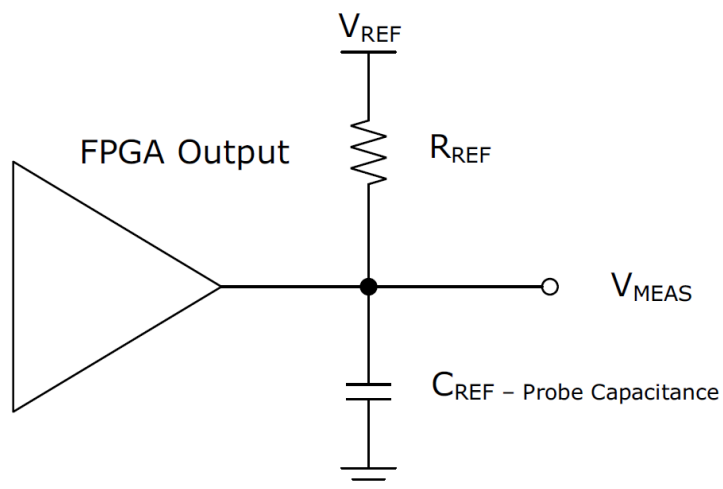
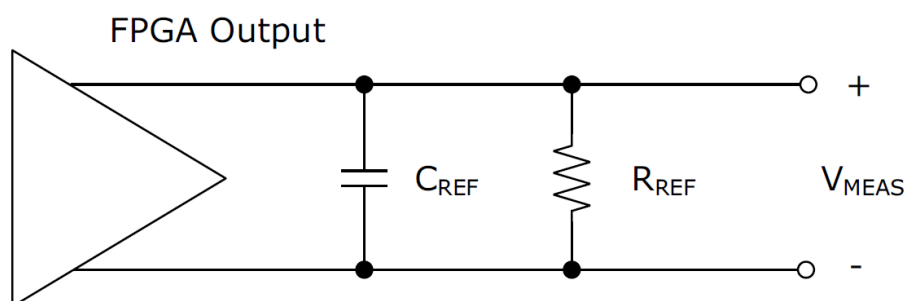
Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

Figure 2 • Output Delay Measurement—Differential Test Setup


7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	-1	Unit
LVDS18	1250	1250	Mbps
RDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Standard	STD	–1	Unit
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps
LVC MOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with $V_{ID} \geq 200$ mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps

Standard	STD	–1	Unit
LVC MOS12 (8 mA)	250	300	Mbps

Table 27 • GPIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
LVDS25/LCMDS25	1250	1250	Mbps
LVDS33/LCMDS33	1250	1600	Mbps
RSDS25	800	800	Mbps
MINILVDS25	800	800	Mbps
SUBLVDS25	800	800	Mbps
PPDS25	800	800	Mbps
SLVSE15	500	500	Mbps
BUSLVDS25	500	500	Mbps
MLVDS25	500	500	Mbps
LVPECL33	500	500	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL25I (differential)	800	800	Mbps
SSTL25II (differential)	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL18I (differential)	800	800	Mbps
SSTL18II (differential)	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
SSTL15I (differential)	800	1066	Mbps
SSTL15II (differential)	800	1066	Mbps
HSTL15I	900	900	Mbps
HSTL15II	900	900	Mbps
HSTL15I (differential)	900	900	Mbps
HSTL15II (differential)	900	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18I (differential)	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
PCI	500	500	Mbps
LVTTTL33 (20 mA)	500	500	Mbps
LVC MOS33 (20 mA)	500	500	Mbps
LVC MOS25 (16 mA)	500	500	Mbps
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps
LVC MOS12 (8 mA)	250	300	Mbps
MIPIE25	500	500	Mbps

7.1.6 User I/O Switching Characteristics

The following section describes characteristics for user I/O switching.

For more information about user I/O timing, see the *PolarFire I/O Timing Spreadsheet* (to be released).

7.1.6.1 I/O Digital

The following tables provide information about I/O digital.

Table 30 • I/O Digital Receive Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
F _{MAX}	RX_SDR_G_A	Rx SDR							MHz	From a global clock source, aligned
F _{MAX}	RX_SDR_L_A	Rx SDR							MHz	From a lane clock source, aligned
F _{MAX}	RX_SDR_G_C	Rx SDR							MHz	From a global clock source, centered
F _{MAX}	RX_SDR_L_C	Rx SDR							MHz	From a lane clock source, centered

Table 31 • I/O Digital Receive Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
F _{MAX}	RX_DDR_G_A	Rx DDR		335			335	MHz	MHz	From a global clock source, aligned
F _{MAX}	RX_DDR_L_A	Rx DDR		250			250		MHz	From a lane clock source, aligned
F _{MAX}	RX_DDR_G_C	Rx DDR		335			335		MHz	From a global clock source, centered
F _{MAX}	RX_DDR_L_C	Rx DDR		250			250		MHz	From a lane clock source, centered
F _{MAX} 2:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T _{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew ¹	F _{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F _{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F _{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F _{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion ²	T _{DCB}	90	90	90	90	ps	HSIO without bridging
	T _{DCB}	115	115	115	115	ps	HSIO with bridging
	T _{DCB}	90	90	90	90	ps	GPIO without bridging
	T _{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2

PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{INPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDET1}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDET2}	10	50	125	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

7.3 Fabric Specifications

The following section describes specifications for the fabric.

7.3.1 Math Blocks

The following tables describe math block performance.

Table 41 • Math Block Performance Extended Commercial Range (0 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	370	470	440	500	MHz
		18 × 18 multiplication summed with 48-bit input	370	470	440	500	MHz
		18 × 19 multiplier pre-adder ROM mode	365	465	435	500	MHz
		Two 9 × 9 multiplication	370	470	440	500	MHz
		9 × 9 dot product (DOTP)	370	470	440	500	MHz
		Complex 18 × 19 multiplication	360	455	430	500	MHz

Table 42 • Math Block Performance Industrial Range (–40 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	365	465	435	500	MHz
		18 × 18 multiplication summed with 48-bit input	365	465	435	500	MHz
		18 × 19 multiplier pre-adder ROM mode	355	460	430	500	MHz
		Two 9 × 9 multiplication	365	465	435	500	MHz
		9 × 9 DOTP	365	465	435	500	MHz
		Complex 18 × 19 multiplication	350	450	425	500	MHz

7.5.7 CPRI

The following table describes CPRI.

Table 66 • CPRI

	Data Rate	Min	Max	Unit
Total transmit jitter	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps ¹			UI
Receive jitter tolerance	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps ¹			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

7.5.8 JESD204B

The following table describes JESD204B.

Table 67 • JESD204B

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	3.125 Gbps		0.35	UI
	6.25 Gbps		0.3	UI
	12.5 Gbps ¹			UI
Receive jitter tolerance	3.125 Gbps	0.56		UI
	6.25 Gbps	0.6		UI
	12.5 Gbps ¹			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

7.6 Non-Volatile Characteristics

The following section describes non-volatile characteristics.

7.6.1 FPGA Programming Cycle and Retention

The following table describes FPGA programming cycle and retention.

Table 68 • FPGA Programming Cycles vs Retention Characteristics

Programming T _i	Programming Cycles, Max	Retention Years	Retention Years at T _i
0 °C to 85 °C	1000	20	85 °C
0 °C to 100 °C	500	20	100 °C
–20 °C to 100 °C	500	20	100 °C
–40 °C to 100 °C	500	20	100 °C
–40 °C to 85 °C	1000	16	100 °C
–40 °C to 55 °C	2000	12	100 °C

Note: Power supplied to the device must be valid during programming operations such as programming and verify . Programming recovery mode is available only for in-application programming mode and requires an external SPI flash.

7.6.2 FPGA Programming Time

The following tables describe FPGA programming time.

Table 69 • Master SPI Programming Time (IAP)

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	17	25	s
		MPF300T, TL, TS, TLS	26	32	s
		MPF500T, TL, TS, TLS			s

Table 70 • Slave SPI Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	41 ¹		s
		MPF300T, TL, TS, TLS	50 ¹	60	s
		MPF500T, TL, TS, TLS			s

1. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. Bitstream stored in DDR. DirectC version 4.1.

Table 71 • JTAG Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS		56	s
		MPF300T, TL, TS, TLS ¹		95	s
		MPF500T, TL, TS, TLS			s

1. Programmer: FlashPro5 with TCK 10 MHz. PC Configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ¹			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53 ¹	s
	MPF300T, TL, TS, TLS	90 ¹	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37 ²	s
	MPF300T, TL, TS, TLS	55 ²	s
	MPF500T, TL, TS, TLS		s

1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours over the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF500T, TL, TS, TLS						

Notes:

- FlashPro4 4 MHz TCK.
- FlashPro5 10 MHz TCK.
- PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

Table 83 • Verify System Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
In application verify by index	T _{IAP_Ver_Index}	44H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s
In application verify by SPI address	T _{IAP_Ver_Addr}	45H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s

7.6.8**Authentication Time**

The following tables describe authentication system service time.

Table 84 • Authentication Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
Bitstream Authentication	T _{BIT_AUTH}	22H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			s
IAP Image Authentication	T _{IAP_AUTH}	23H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			s

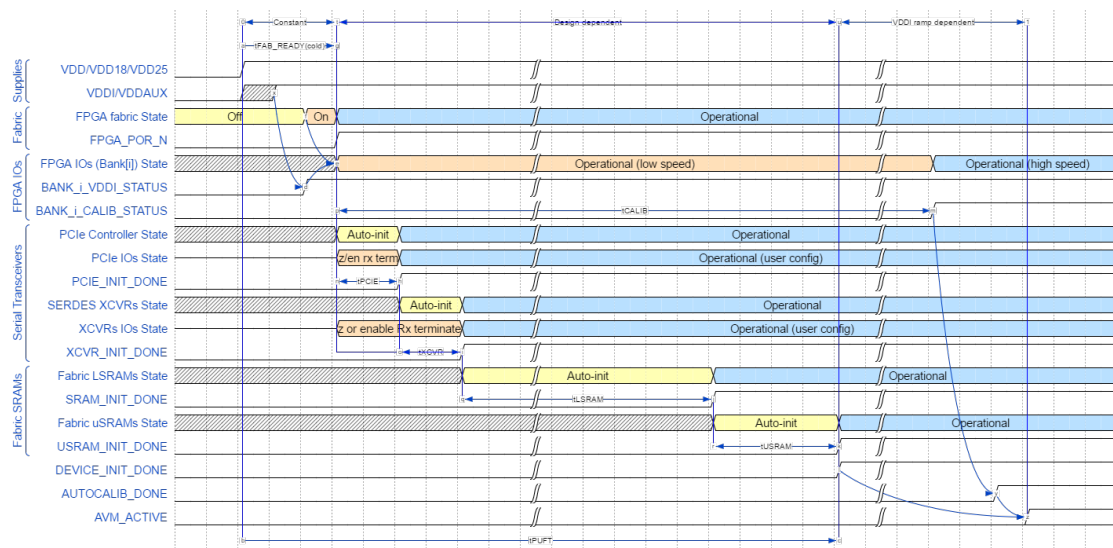
7.6.9**Secure NVM Performance**

The following table describes secure NVM performance.

Table 85 • sNVM Read/Write Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Plain text programming		7.0	7.2	7.9	ms	
Authenticated text programming		7.2	7.4	9.4	ms	
Authenticated and encrypted text programming		7.2	7.4	9.4	ms	
Authentication R/W 1st access from power-up overhead	T _{PUF_OVHD}		100	111	ms	From T _{FAB_READY}
Plain text read		7.67	7.79	8.2	μs	

Figure 5 • Cold Reset Timing

**Notes:**

- The previous diagram shows the case where VDDI/VDDAUX of I/O banks are powered either before or sufficiently soon after VDD/VDD18/VDD25 that the I/O bank enable time is measured from the assertion time of VDD/VDD18/VDD25 (that is, the PUFT specification). If VDDI/VDDAUX of I/O banks are powered sufficiently after VDD/VDD18/VDD25, then the I/O bank enable time is measured from the assertion of BANK_i_VDDI_STATUS, rather than being measured relative to FABRIC_POR_N negation.
- AUTOCALIB_DONE assertion indicates the completion of calibration for any I/O banks specified by the user for auto-calibration. AUTOCALIB_DONE asserts independently of DEVICE_INIT_DONE. It may assert before or after DEVICE_INIT_DONE and is determined by the following:
 - How long after VDD/VDD18/VDD25 that VDDI/VDDAUX are powered on. Note that if any of the user-specified I/O banks are not powered on within the auto-calibration timeout window, then AUTOCALIB_DONE doesn't assert until after this timeout.
 - The specified ramp times of VDDI of each I/O bank designated for auto-calibration.
 - How much auto-initialization is to be performed for the PCIe, SERDES transceivers, and fabric LSRAMs.
- If any of the I/O banks specified for auto-calibration do not have their VDDI/VDDAUX powered on within the auto-calibration timeout window, then it will be approximately auto-calibrated whenever VDDI/VDDAUX is subsequently powered on. To obtain an accurate calibration however, on such IO banks, it is necessary to initiate a re-calibration (using CALIB_START from fabric).
- AVM_ACTIVE only asserts if avionics mode is being used. It is asserted when the later of DEVICE_INIT_DONE or AUTOCALIB_DONE assert.

7.9.2**Warm Reset Initialization Sequence**

The following warm reset timing diagram shows the initialization sequencing of the device when either DEVRST_N or TAMPER_RESET_DEVICE signals are asserted.

Table 101 • Cold and Warm Boot

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from T _{FAB_READY} to ready to program through JTAG/SPI-Slave		0	0	0	ms	
The time from T _{FAB_READY} to auto-update start			T _{PUF_OVHD} ¹	T _{PUF_OVHD} ¹	ms	
The time from T _{FAB_READY} to programming recovery start			T _{PUF_OVHD} ¹	T _{PUF_OVHD} ¹	ms	
The time from T _{FAB_READY} to the tamper flags being available	T _{TAMPER_READY}	0	0	0	ms	
The time from T _{FAB_READY} to the Athena Crypto co-processor being available (for S devices only)	T _{CRYPTO_READY}	0	0	0	ms	

1. Programming depends on the PUF to power up. Refer to T_{PUF_OVHD} at section [Secure NVM Performance](#) (see page 58).

7.9.8 I/O Calibration

The following tables specify the initial I/O calibration time for the fastest and slowest supported VDDI ramp times of 0.2 ms to 50 ms, respectively. This only applies to I/O banks specified by the user to be auto-calibrated.

Table 102 • I/O Initial Calibration Time (TCALIB)

Ramp Time	Min (ms)	Max (ms)	Condition
0.2 ms	0.98	2.63	Applies to HSIO and GPIO banks
50 ms	41.62	62.19	Applies to HSIO and GPIO banks

Notes:

- The user may specify any VDDI ramp time in the range specified above. The nominal initial calibration time is given by the specified VDDI ramp time plus 2 ms.
- In order for IO calibration to start, VDDI and VDDAUX of the I/O bank must be higher than the trip point levels specified in [I/O-Related Supplies](#) (see page 66).

Table 103 • I/O Fast Recalibration Time (TRECALIB)

I/O Type	Min (ms)	Typ (ms)	Max (ms)	Condition
GPIO bank	0.16	0.20	0.24	GPIO configured for 3.3 V operation
HSIO bank	0.20	0.25	0.30	HSIO configured for 1.8 V operation

Note: In order to obtain fast re-calibration, the user must assert the relevant clock request signal from the FPGA fabric to the I/O bank controller.

The following table describes the time to enter Flash*Freeze Mode and to exit Flash*Freeze mode.

1. With DPA counter measures.

Table 115 • HMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
HMAC-SHA-256 ¹ , 256-bit key	512	7477	2361
	64K	88367	2099
HMAC-SHA-384 ¹ , 384-bit key	1024	13049	2257
	64K	106103	2153

1. With DPA counter measures.

Table 116 • CMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-CMAC-256 ¹ (message is only authenticated)	128	446	9058
	64K	45494	111053

1. With DPA counter measures.

Table 117 • KEY TREE

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
128-bit nonce + 8-bit optype		102457	2751
256-bit nonce + 8-bit optype		103218	2089

Table 118 • SHA

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
SHA-1 ¹	512	2386	1579
	64K	77576	990
SHA-256 ¹	512	2516	884
	64K	84752	938
SHA-384 ¹	1024	4154	884
	64K	100222	938
SHA-512 ¹	1024	4154	881
	64K	100222	935

1. With DPA counter measures.

Table 119 • ECC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
ECDSA SigGen, P-384/SHA-384 ¹	1024	12528912	6944
	8K	12540448	5643
ECDSA SigGen, P-384/SHA-384	1024	5502928	6155